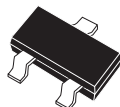


CMPT2484
NPN SILICON
LOW NOISE TRANSISTOR



SOT-23 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT2484 type is an NPN silicon low noise transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for low noise amplifier applications.

Marking Code is C1U.

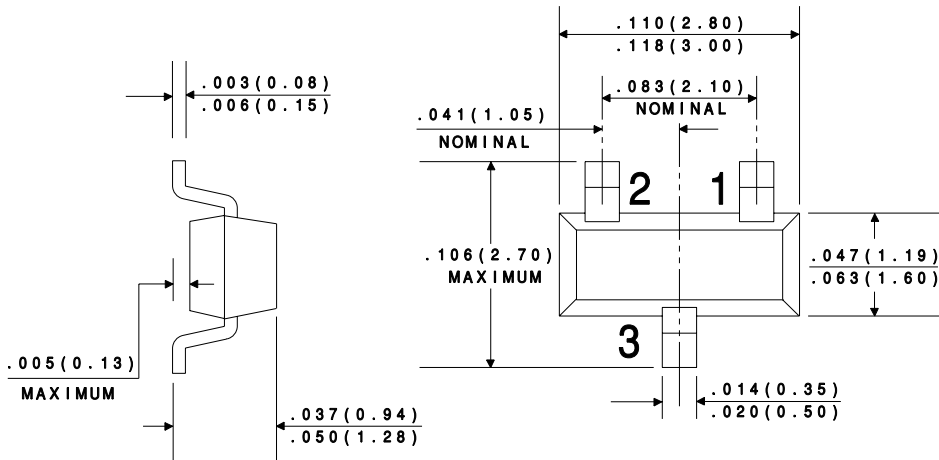
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	60	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current	I_C	50	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	θ_{JA}	357	$^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=45\text{V}$		10	nA
I_{CBO}	$V_{CB}=45\text{V}, T_A=150^{\circ}\text{C}$		10	μA
I_{EBO}	$V_{EB}=5.0\text{V}$		10	nA
BV_{CBO}	$I_C=10\mu\text{A}$	60		V
BV_{CEO}	$I_C=10\text{mA}$	60		V
BV_{EBO}	$I_E=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=1.0\text{mA}, I_B=100\mu\text{A}$		0.35	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$		0.95	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$	250	---	
h_{FE}	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	---	800	
C_{ob}	$V_{CB}=5.0\text{V}, I_E=0, f=1.0\text{MHz}$		6.0	pF
C_{ib}	$V_{EB}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$		6.0	pF
NF	$V_{CE}=5.0\text{V}, I_C=10\mu\text{A}, R_S=10\text{k}\Omega$ $f=1.0\text{kHz}, BW=200\text{Hz}$		3.0	dB

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR